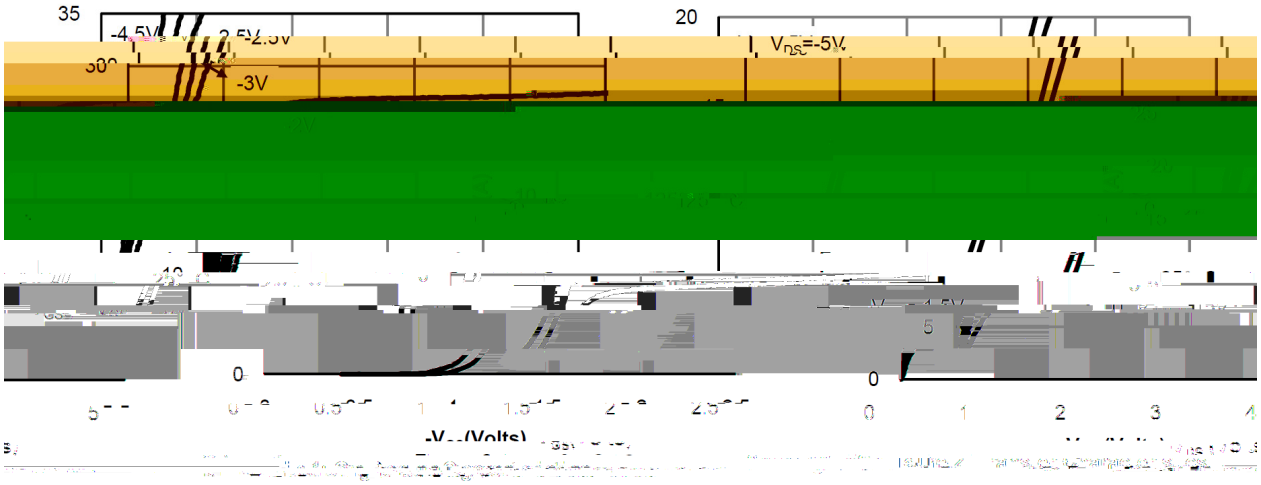
SOT23-3 ṂṂ Ḅ P ঌ MOS ß ѽ Ẓ ㄱ
S- CHANNEL MOSFET in a SOT23-3 Plastic Package.

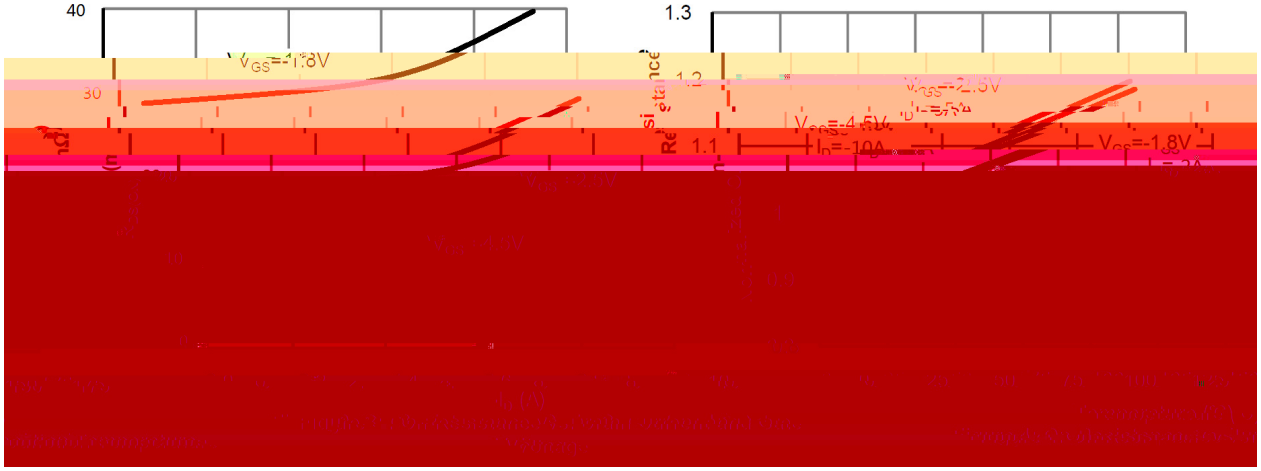
V_{DS} (V) = -20V
I_D = -7.0A
$R_{DS(ON)}$@-4.5VDS0 1 Tf10.4988DS0 1 Tf10.4988

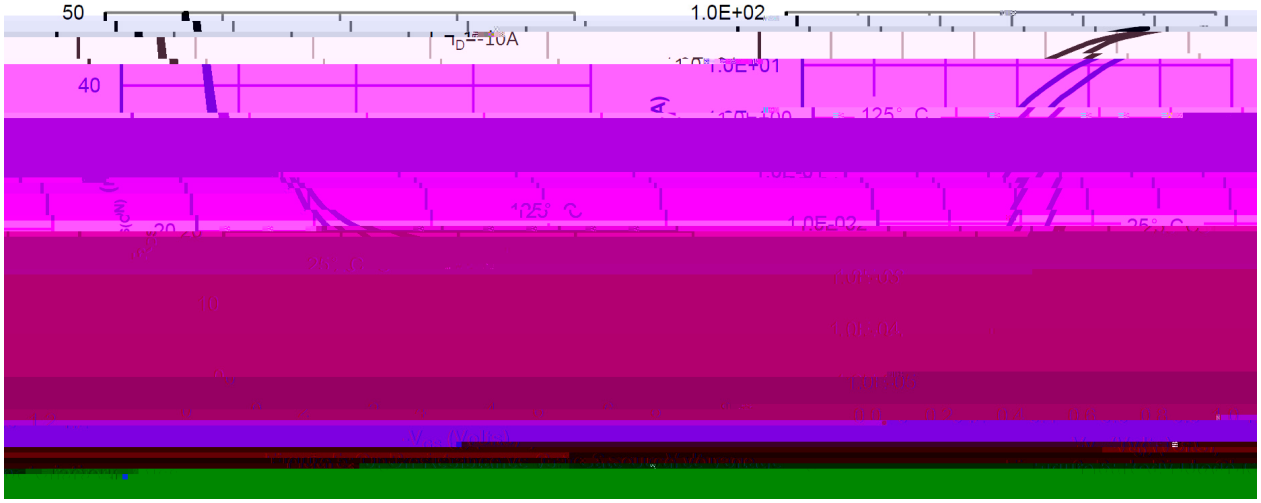
v ″Ω Parameter	ϒ N Symbol	″Ω Ö Rating	D Ч Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±12	V
Continuous Drain Current	I_D	7.0	A
Pulsed Drain Current	I_{DM}	38	A
Avalanche Current	I_{AS}	13	A
Avalanche energy L=0.5mH	E_{AS}	59	mJ

v ̈Ω	ϒ ᴺ	╨ ;ǂ ţ	ϣ ŋ Ө
Parameter	Symbol	Test Conditions	Min

/ Electrical Characteristic Curve







/ Electrical Characteristic Curve

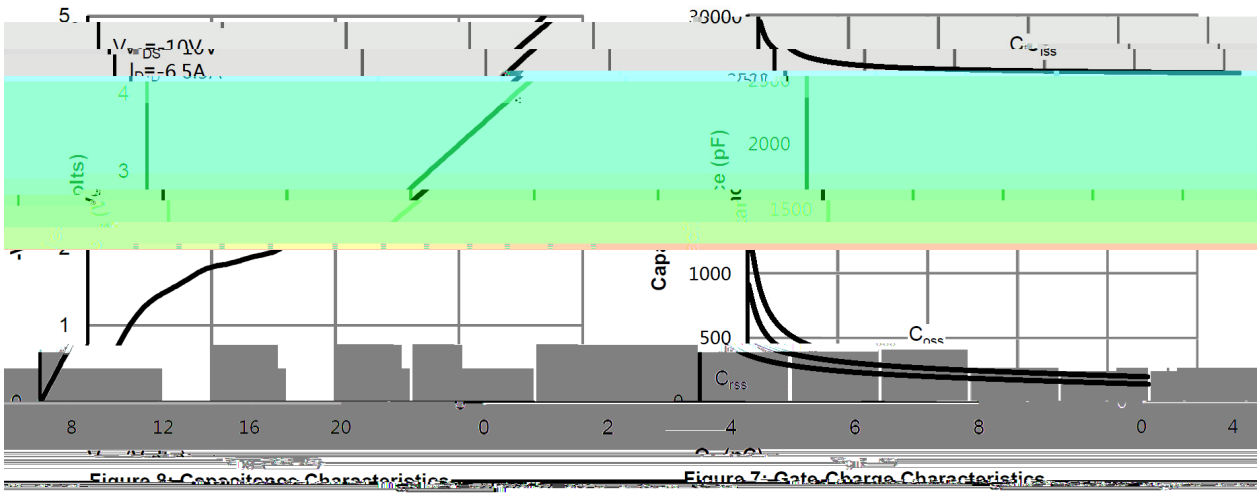
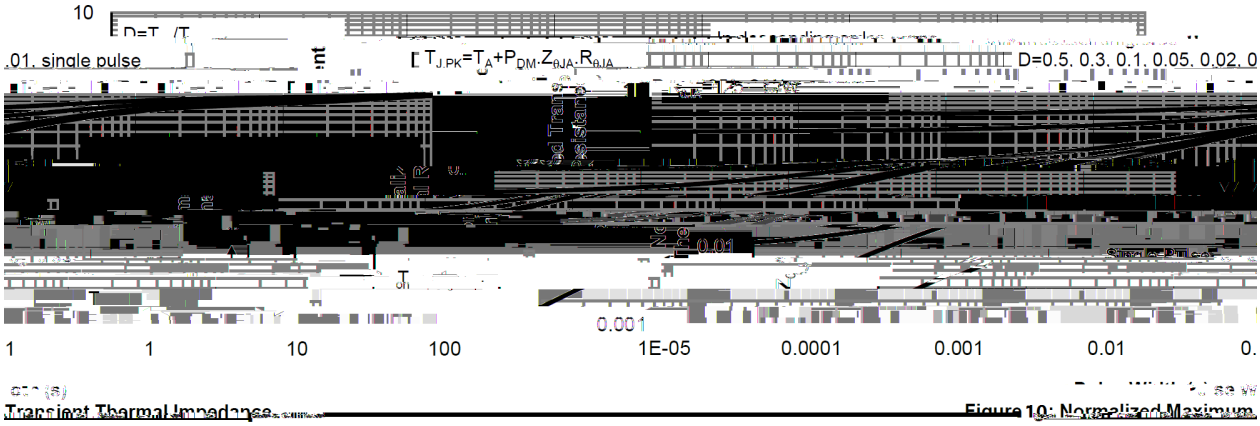


Figure 8: Capacitance Characteristics

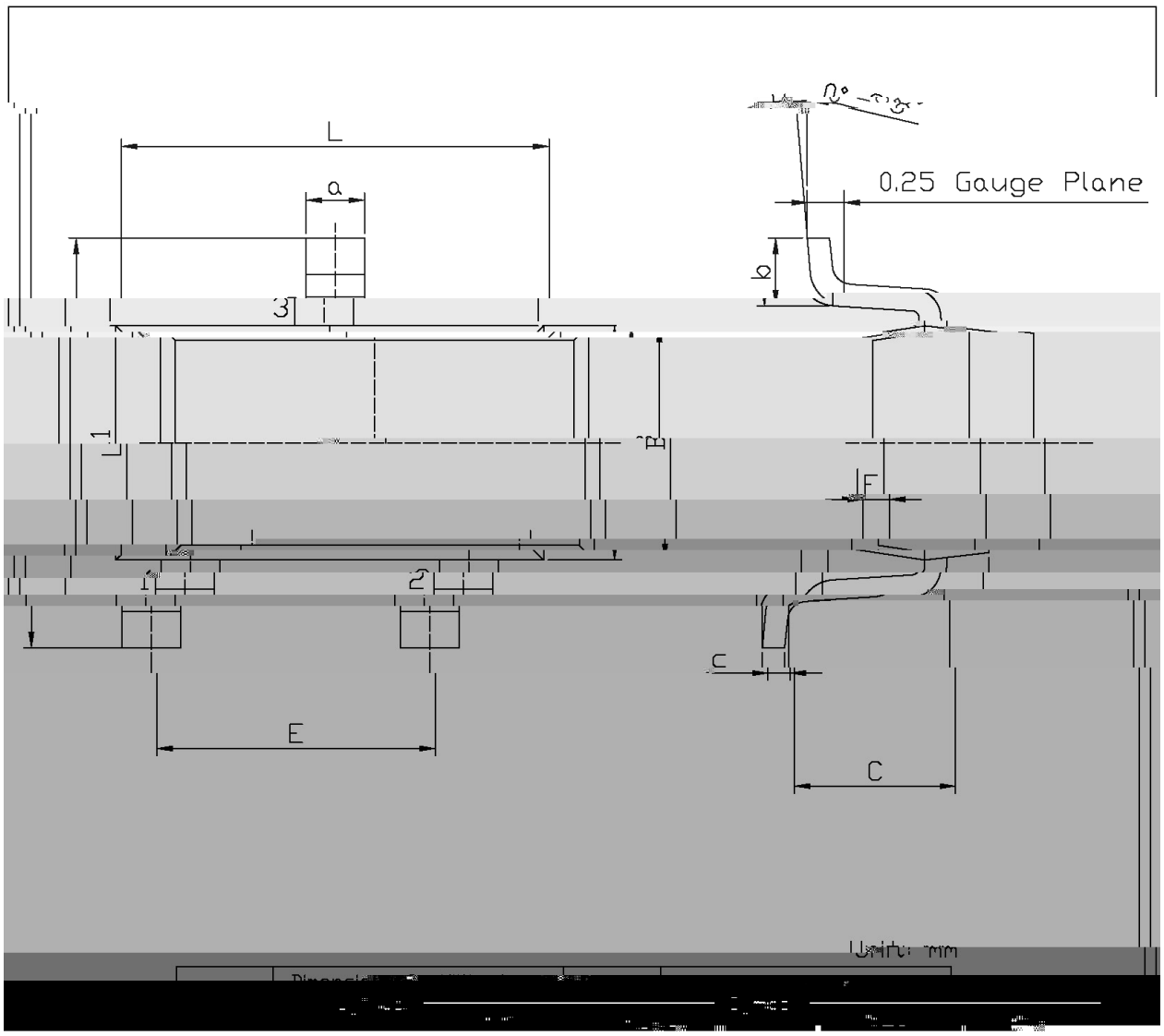
Figure 7: Gate Charge Characteristics



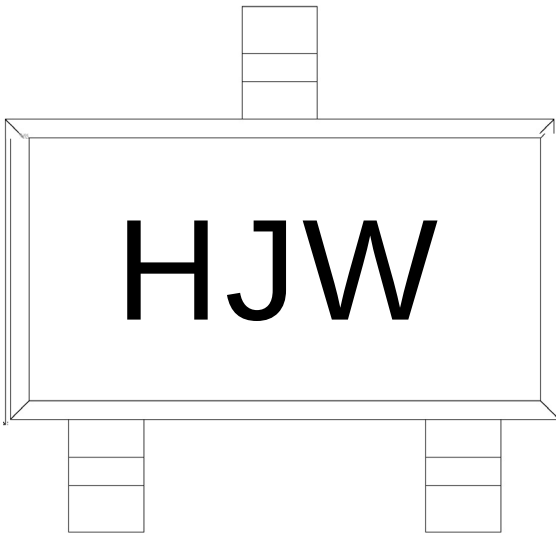
Transient Thermal Impedance

Figure 10: Normalized Maximum

/ Package Dimensions



/ Marking Instructions



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JW χ ᑲᖏ ᘁ ᴺ ᒣᑐ

Note:

H: Company Code

JW: Product Type